Please replace the paragraph beginning at page 2, line 11, with the following rewritten paragraph:

--Figure 3 is an exploded view of a semiconductor device in accordance with the present invention; and--

Please add the following paragraph beginning at page 2, line 13:

--Figure 4 is a side sectional view of a bumped die.--

Please replace the paragraph beginning at page 2, line 26, with the following rewritten paragraph:

--In accordance with a preferred embodiment of the present invention, dies 30, 32 are bumped dies, which are one-piece items. As can be seen in Figure 4, a bumped die includes the die, an "under bump" material 40 that serves as an intermediate layer between the top surface of the die and solder bump 41. Preferably, the under bump material is one of TiW, Cu, Au or an equivalent. In the example illustrated in Figure 4, the under bump material is broken into three layers - Cu plating 40a, sputtered Cu 40b, and sputtered Ti 40c.--

Please replace the paragraph beginning at page 3, line 1, with the following rewritten paragraph:

--A drain clip assembly 50 is attached to drain region 51 of the first die preferably with solder. The drain clip assembly includes a top die drain clip 52 and a side rail leadframe 53. Solder paste is dispensed on the drain region of the first die and into elongated v-groove 54 in side rail 53. Clip 52, preferably comprising copper, is supplied, (preferably in reel form) and pick-and-placed onto the die backside such that edge 55 of the copper clip is placed within the elongated v-groove. Thus, the clip provides contact with the first die's drain regions and couples these drain regions to leads 56 of the side rail.--

Please replace the paragraph beginning at page 3, line 15, with the following rewritten paragraph: